Abstracts

Trapping effects in wide-bandgap microwave FETs

S.C. Binari, P.B. Klein and T.E. Kazior. "Trapping effects in wide-bandgap microwave FETs." 2002 MTT-S International Microwave Symposium Digest 02.3 (2002 Vol. III [MWSYM]): 1823-1826 vol.3.

It is well known that trapping effects can limit the output power performance of microwave field-effect transistors. This is particularly true for the wide-bandgap devices. In this paper, we review the various trapping phenomena observed in SiC and GaN-based FETs that contribute to compromised power performance. For both of these material systems, trapping effects associated with both the surface and with the layers underlying the active channel have been identified.

❑ Return to main document.